



### CMKSH-3DO

### SURFACE MOUNT ULTRAMini™ DUAL OPPOSING SILICON SCHOTTKY DIODES



# Central™ Semiconductor Corp.

#### DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKSH-3DO incorporates two (2) galvanically isolated, Low  $V_F$  Silicon Diodes with an opposing Anode/Cathode configuration, in a space saving surface mount package, designed for fast switching applications requiring a low forward voltage drop.

#### MARKING CODE: KDO

#### FEATURES:

- Dual Opposing (DO) Schottky Diodes
- Small ULTRAMini™ SOT-363 Package
- Galvanically Isolated
- Low Forward Voltage (0.58V TYP @ 100mA)

#### MAXIMUM RATINGS: ( $T_A=25^\circ\text{C}$ )

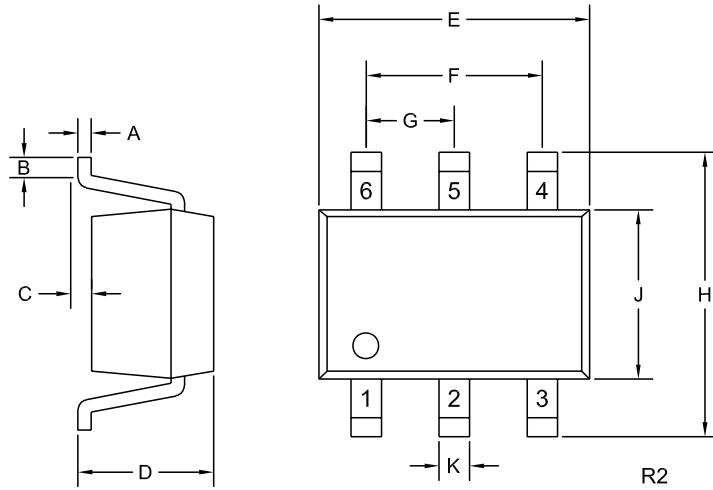
Peak Repetitive Reverse Voltage
Continuous Forward Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
$V_{RRM}$	30	V
$I_F$	100	mA
$P_D$	250	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\Theta_{JA}$	500	$^\circ\text{C/W}$

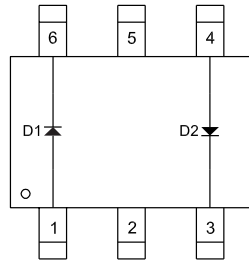
#### ELECTRICAL CHARACTERISTICS PER DIODE: ( $T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=25\text{V}$			500	nA
$I_R$	$V_R=25\text{V}$ ( $T_A=100^\circ\text{C}$ )			100	$\mu\text{A}$
$BV_R$	$I_R=100\mu\text{A}$	30			V
$V_F$	$I_F=2.0\text{mA}$			0.33	V
$V_F$	$I_F=15\text{mA}$			0.45	V
$V_F$	$I_F=100\text{mA}$		0.58	1.00	V
$C_T$	$V_R=0, f=1.0\text{MHz}$		7.0		pF
$t_{rr}$	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

**SOT-363 CASE - MECHANICAL OUTLINE**



**PIN CONFIGURATION**



**LEAD CODE:**

- 1) ANODE D1
- 2) NC
- 3) CATHODE D2
- 4) ANODE D2
- 5) NC
- 6) CATHODE D1

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SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)